



# N-Channel NexFET™ Power MOSFET

# **FEATURES**

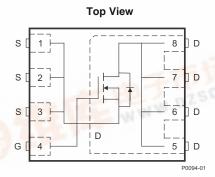
- Ultralow Q<sub>q</sub> and Q<sub>qd</sub>
- Low Thermal Resistance
- Avalanche Rated
- SON 5-mm × 6-mm Plastic Package

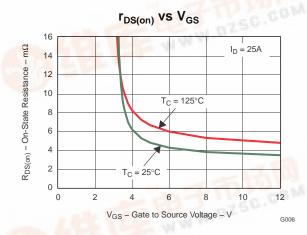
### **APPLICATIONS**

- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems
- Optimized for Control FET Applications

## DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.





### **PRODUCT SUMMARY**

$V_{DS}$	Drain-to-source voltage	25	m	V
$Q_g$	Gate charge, total (4.5 V)	6.7	nC	
$Q_{gd}$	Gate charge, gate-to-drain	1.9		nC
-	Drain-to-source on-resistance	$V_{GS} = 4.5 \text{ V}$	5.4	mΩ
r <sub>DS(on)</sub>	Dialit-to-source off-fesistance	V <sub>GS</sub> = 10 V	3.6	mΩ
V <sub>GS(th)</sub>	Threshold voltage	1.8		V

#### ORDERING INFORMATION

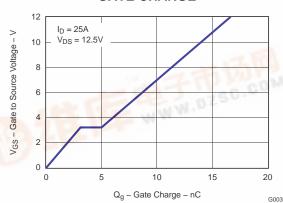
Device	Package	Media	Qty	Ship
CSD16408Q5	SON 5-mm × 6-mm plastic package	13-inch (33-cm) reel	2500	Tape and reel

#### ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5°C unless otherwise stated	VALUE	UNIT
$V_{DS}$	Drain-to-source voltage	25	V
V <sub>GS</sub>	Gate-to-source voltage	-12 to 16	V
WE	Continuous drain current, T <sub>C</sub> = 25°C	113	Α
I <sub>D</sub>	Continuous drain current <sup>(1)</sup>	22	Α
I <sub>DM</sub>	Pulsed drain current, T <sub>A</sub> = 25°C <sup>(2)</sup>	141	Α
$P_D$	Power dissipation <sup>(1)</sup>	3.1	W
T <sub>J</sub> , T <sub>STG</sub>	Operating junction and storage temperature range	-55 to 150	°C
E <sub>AS</sub>	Avalanche energy, single-pulse $I_D = 23 \text{ A}, L = 0.1 \text{ mH}, R_G = 25 \Omega$	126	mJ

- (1) Typical  $R_{\theta JA} = 41^{\circ}\text{C/W on 1-inch}^2$  (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB
- (2) Pulse duration ≤300 μs, duty cycle ≤2%

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## **ELECTRICAL CHARACTERISTICS**

$I_A = 25^{\circ}$	C unless otherwise stated					
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static C	haracteristics					
$BV_{DSS}$	Drain-to-source voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	25			V
$I_{DSS}$	Drain-to-source leakage	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}$			1	μΑ
$I_{GSS}$	Gate-to-source leakage	$V_{DS} = 0 \text{ V}, V_{GS} = -12 \text{ V to } 16 \text{ V}$			100	nA
$V_{GS(th)}$	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.4	1.8	2.1	V
-	Drain-to-source on-resistance	$V_{GS} = 4.5 \text{ V}, I_D = 25 \text{ A}$		5.4	6.8	$m\Omega$
r <sub>DS(on)</sub>	Diam-to-source on-resistance	$V_{GS} = 10 \text{ V}, I_D = 25 \text{ A}$		3.6	4.5	$m\Omega$
9 <sub>fs</sub>	Transconductance	$V_{DS} = 15 \text{ V}, I_D = 25 \text{ A}$		60		S
Dynami	c Characteristics					
C <sub>ISS</sub>	Input capacitance			990	1300	pF
Coss	Output capacitance	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 12.5 V , f = 1 MHz		760	1000	pF
C <sub>RSS</sub>	Reverse transfer capacitance			75	100	pF
R <sub>g</sub>	Series gate resistance			0.8	1.6	Ω
Qg	Gate charge total (4.5 V)			6.7	8.9	nC
Q <sub>gd</sub>	Gate charge, gate-to-drain	V 40.5 V 1 05.A		1.9		nC
$Q_{gs}$	Gate charge, gate-to-source	V <sub>DS</sub> = 12.5 V, I <sub>D</sub> = 25 A		3.1		nC
Q <sub>g(th)</sub>	Gate charge at Vth			1.8		nC
Q <sub>OSS</sub>	Output charge	V <sub>DS</sub> = 13 V, V <sub>GS</sub> = 0 V		15.7		nC
t <sub>d(on)</sub>	Turnon delay time			11.3		ns
t <sub>r</sub>	Rise time	V <sub>DS</sub> = 12.5 V, V <sub>GS</sub> = 4.5 V,		25		ns
t <sub>d(off)</sub>	Turnoff delay time	$I_D = 20 \text{ A}, R_G = 2 \Omega$		11		ns
t <sub>f</sub>	Fall time			10.8		ns
Diode C	haracteristics	·				
V <sub>SD</sub>	Diode forward voltage	I <sub>S</sub> = 25 A, V <sub>GS</sub> = 0 V		0.8	1	V
Q <sub>rr</sub>	Reverse recovery charge	$V_{DD} = 13 \text{ V}, I_F = 2 \text{ 5A}, di/dt = 300 \text{ A/}\mu\text{s}$		17		nC
t <sub>rr</sub>	Reverse recovery time	V <sub>DD</sub> = 13 V, I <sub>F</sub> = 25 A, di/dt = 300 A/μs		21		ns

## THERMAL CHARACTERISTICS

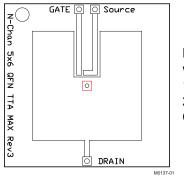
 $T_{\Delta} = 25^{\circ}C$  unless otherwise stated

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	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case (1)			1.9	°C/W
$R_{\theta,JA}$	Thermal Resistance Junction to Ambient <sup>(1)</sup> (2)			51	°C/W

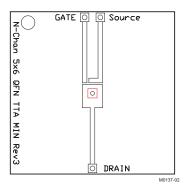
 $R_{\theta JC}$  is determined with the device mounted on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB.  $R_{\theta JC}$  is specified by design, whereas  $R_{\theta JA}$  is determined by the user's board design. Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.



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Max  $R_{\theta JA} = 51^{o}C/W$  when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max  $R_{\theta JA} = 125^{o} C/W$  when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

## TYPICAL MOSFET CHARACTERISTICS

 $T_A = 25$ °C unless otherwise stated

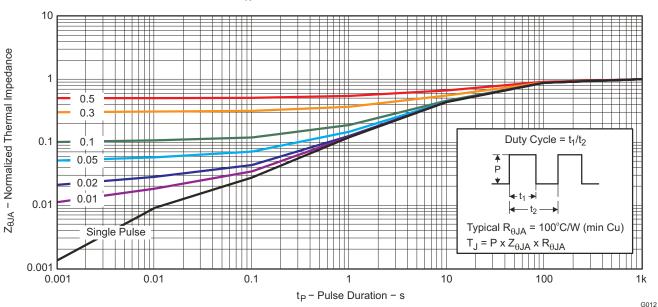


Figure 1. Transient Thermal Impedance

# TYPICAL MOSFET CHARACTERISTICS (continued)

 $T_A = 25$ °C unless otherwise stated

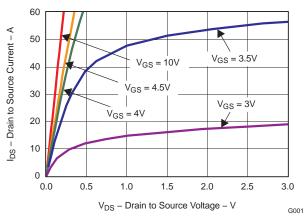


Figure 2. Saturation Characteristics

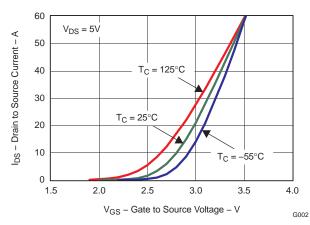


Figure 3. Transfer Characteristics

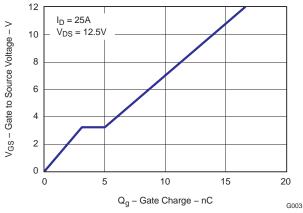


Figure 4. Gate Charge

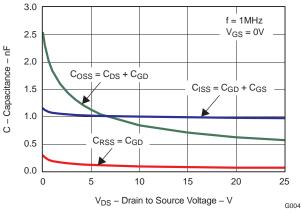


Figure 5. Capacitance

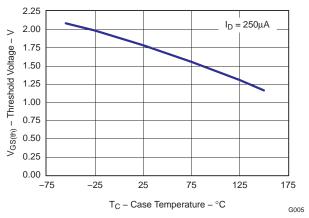


Figure 6. Threshold Voltage vs. Temperature

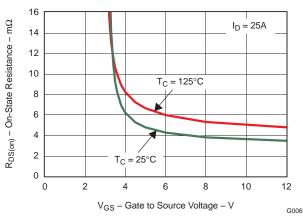


Figure 7. On-State Resistance vs. Gate-to-Source Voltage



# TYPICAL MOSFET CHARACTERISTICS (continued)

## T<sub>A</sub> = 25°C unless otherwise stated

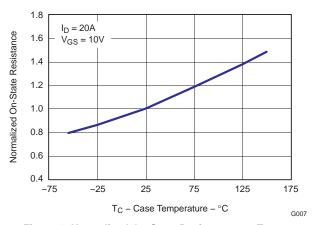


Figure 8. Normalized On-State Resistance vs. Temperature

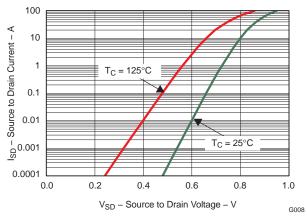


Figure 9. Typical Diode Forward Voltage

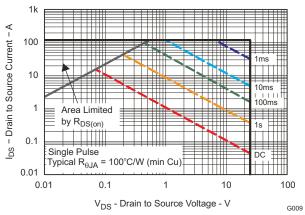


Figure 10. Maximum Safe Operating Area

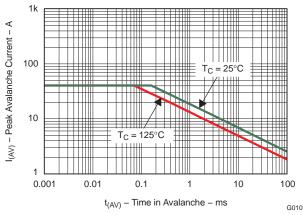


Figure 11. Single-Pulse Unclamped Inductive Switching

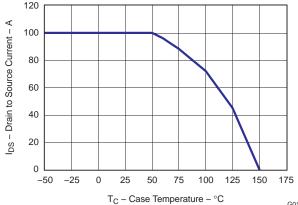
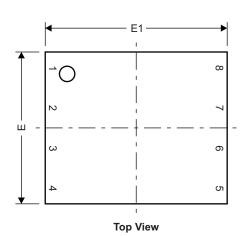


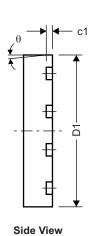
Figure 12. Maximum Drain Current vs. Temperature

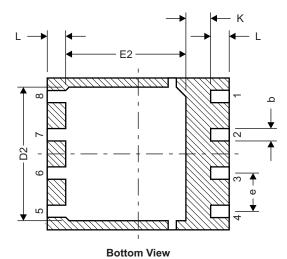


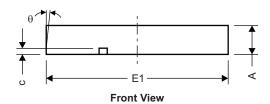
# **MECHANICAL DATA**

# **Q5 Package Dimensions**









M0140-01

DIM	MILLIM	ETERS	INCHES		
DIIVI	MIN	MAX	MIN	MAX	
Α	0.950	1.050	0.037	0.039	
b	0.360	0.460	0.014	0.018	
С	0.150	0.250	0.006	0.010	
c1	0.150	0.250	0.006	0.010	
D1	4.900	5.100	0.193	0.201	
D2	4.320	4.520	0.170	0.178	
E	4.900	5.100	0.193	0.201	
E1	5.900	6.100	0.232	0.240	
E2	3.920	4.12	0.154	0.162	
е	1.27	' typ	0.0	050	
L	0.510	0.710	0.020	0.028	
θ	0.00	-	_	_	



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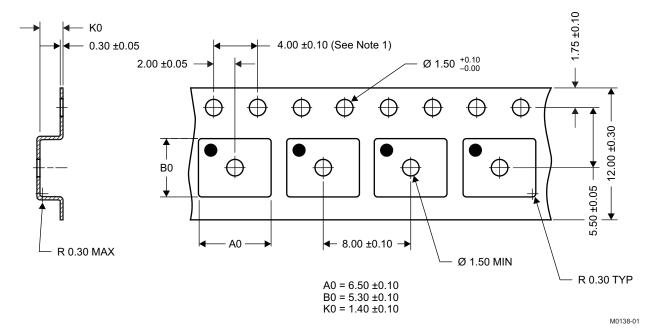
### SLPS228A - OCTOBER 2009-REVISED SEPTEMBER 2010

Recommended PCB Pattern							
F6 - F1	F7						
F10 — F10	M0139-01						

DIM	MILLIM	IETERS	INCHES		
DIN	MIN	MAX	MIN	MAX	
F1	6.205	6.305	0.244	0.248	
F2	4.46	4.56	0.176	0.18	
F3	4.46	4.56	0.176	0.18	
F4	0.65	0.7	0.026	0.028	
F5	0.62	0.67	0.024	0.026	
F6	0.63	0.68	0.025	0.027	
F7	0.7	0.8	0.028	0.031	
F8	0.65	0.7	0.026	0.028	
F9	0.62	0.67	0.024	0.026	
F10	4.9	5	0.193	0.197	
F11	4.46	4.56	0.176	0.18	

For recommended circuit layout for PCB designs, see application note Reducing Ringing Through PCB Layout Techniques (SLPA005).

## **Q5 Tape and Reel Information**



#### Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket
- 6. MSL1 260°C (IR and convection) PbF reflow compatible



# **REVISION HISTORY**

C	Changes from Revision Original (October 2009) to Revision A						
•	Deleted environmental bullets from features list	1					
•	Deleted package marking section from end of data sheet	7					



## PACKA

#### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/ Ball Finish	MSL Pe
CSD16408Q5	ACTIVE	SON	DQH	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retard in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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Microcontrollers	microcontroller.ti.com	Security	www.ti.com/security
RFID	www.ti-rfid.com	Space, Avionics & Defense	www.ti.com/space-avionics-defense
RF/IF and ZigBee® Solutions	www.ti.com/lprf	Video and Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless-apps